

# **Excellent Integrated System Limited**

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Diodes Incorporated DMG6402LDM-7

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**Distributor of Diodes Incorporated: Excellent Integrated System Limited** Datasheet of DMG6402LDM-7 - MOSFET N-CH 30V 5.3A SOT26 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



### NOT RECOMMENDED FOR NEW DESIGN **USE DMG6402LVT**



# DMG6402LDM

N-CHANNEL ENHANCEMENT MODE MOSFET

# **Features**

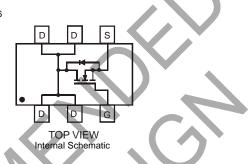
- Low R<sub>DS(ON)</sub>
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 2)

### **Mechanical Data**

- Case: SOT-26 •
- Case Material Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 2
- Ordering Information: See page 2
- Weight: 0.008 grams (approximate) •

SOT-26





### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

| Characteris                       | tic             |  | Symbol           | Value      | Unit |
|-----------------------------------|-----------------|--|------------------|------------|------|
| Drain-Source Voltage              |                 |  | V <sub>DSS</sub> | 30         | V    |
| Gate-Source Voltage               |                 |  | V <sub>GSS</sub> | ±20        | V    |
| Continuous Drain Current (Note 3) | Steady<br>State | T <sub>A</sub> = 25°C<br>T <sub>A</sub> = 70°C | ID               | 5.3<br>4.2 | А    |
| Pulsed Drain Current (Note 4)     |                 |  | IDM              | 31         | A    |

# **Thermal Characteristics**

| Characteristic   | Symbol                            | Value       | Unit |
|--|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 3)                                     | PD                                | 1.12        | W    |
| Thermal Resistance, Junction to Ambient $T_A = 25^{\circ}C$ (Note 3) | R <sub>0JA</sub>                  | 111         | °C/W |
| Operating and Storage Temperature Range                              | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

Notes: 1. No purposefully added lead.

- Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
  Device mounted on FR-4 PCB, with minimum recommended pad layout.
  Repetitive Rating, pulse width limited by junction temperature.





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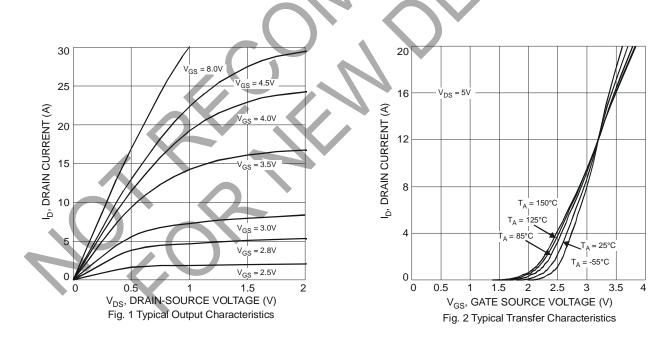
DMG6402LDM

# **Electrical Characteristics** $@T_A = 25^{\circ}C$ unless otherwise specified

| Characteristic  | Symbol                   | Min | Тур      | Max      | Unit    | Test Condition  |
|---|--------------------------|-----|----------|----------|---------|---|
| OFF CHARACTERISTICS (Note 5)                          |                          |     |          |          |         |   |
| Drain-Source Breakdown Voltage                        | <b>BV</b> <sub>DSS</sub> | 30  | -        | -        | V       | $V_{GS} = 0V, I_{D} = 250\mu A$                           |
| Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C | I <sub>DSS</sub>         | -   | -        | 1.0      | $\mu A$ | $V_{DS} = 30V, V_{GS} = 0V$                               |
| Gate-Source Leakage                                   | I <sub>GSS</sub>         | -   | -        | ±100     | nA      | $V_{GS} = \pm 20V, V_{DS} = 0V$                           |
| ON CHARACTERISTICS (Note 5)                           |                          |     |          |          |         |   |
| Gate Threshold Voltage                                | V <sub>GS(th)</sub>      | 1.0 | 1.5      | 2.0      | V       | $V_{DS} = V_{GS}$ , $I_D = 250 \mu A$                     |
| Static Drain-Source On-Resistance                     | Pageau                   | -   | 22<br>32 | 27<br>40 | mΩ      | $V_{GS} = 10V, I_D = 7A$                                  |
|   | R <sub>DS (ON)</sub>     |     |          |          | 111 22  | $V_{GS} = 4.5V, I_D = 5.6A$                               |
| Forward Transfer Admittance                           | Y <sub>fs</sub>          | -   | 10       | -        | S       | $V_{DS} = 5V, I_D = 7A$                                   |
| Diode Forward Voltage                                 | V <sub>SD</sub>          | -   | 0.75     | 1.0      | V       | $V_{GS} = 0V, I_S = 1A$                                   |
| DYNAMIC CHARACTERISTICS (Note 6)                      |                          |     |          |          |         |   |
| Input Capacitance                                     | Ciss                     | -   | 404      | -        | pF      |   |
| Output Capacitance                                    | Coss                     | -   | 52       |          | pF      | V <sub>DS</sub> =15V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz |
| Reverse Transfer Capacitance                          | C <sub>rss</sub>         | -   | 45       | -        | pF      | 1 = 1.00012   |
| Gate Resistance                                       | Rg                       | -   | 1.51     | -        | Ω       | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$                |
| Total Gate Charge                                     | Qg                       | -   | 9.2      | -        | nC      |   |
| Gate-Source Charge                                    | Q <sub>gs</sub>          | -   | 1.2      | -        | nC      | V <sub>GS</sub> =10V, V <sub>DS</sub> = 15V, ID =5.8A     |
| Gate-Drain Charge                                     | Q <sub>gd</sub>          |     | 1.8      |          | nC      |   |
| Turn-On Delay Time                                    | t <sub>D(on)</sub>       | -   | 3.41     | -        | ns      |   |
| Turn-On Rise Time                                     | tr                       | -   | 6.18     | -        | ns      | $V_{DD} = 15V, V_{GS} = 10V,$                             |
| Turn-Off Delay Time                                   | t <sub>D(off)</sub>      |     | 13.92    | -        | ns      | $R_L = 2.6\Omega, R_G = 3\Omega$                          |
| Turn-Off Fall Time                                    | tf                       |     | 2.84     | -        | ns      |   |

Notes:

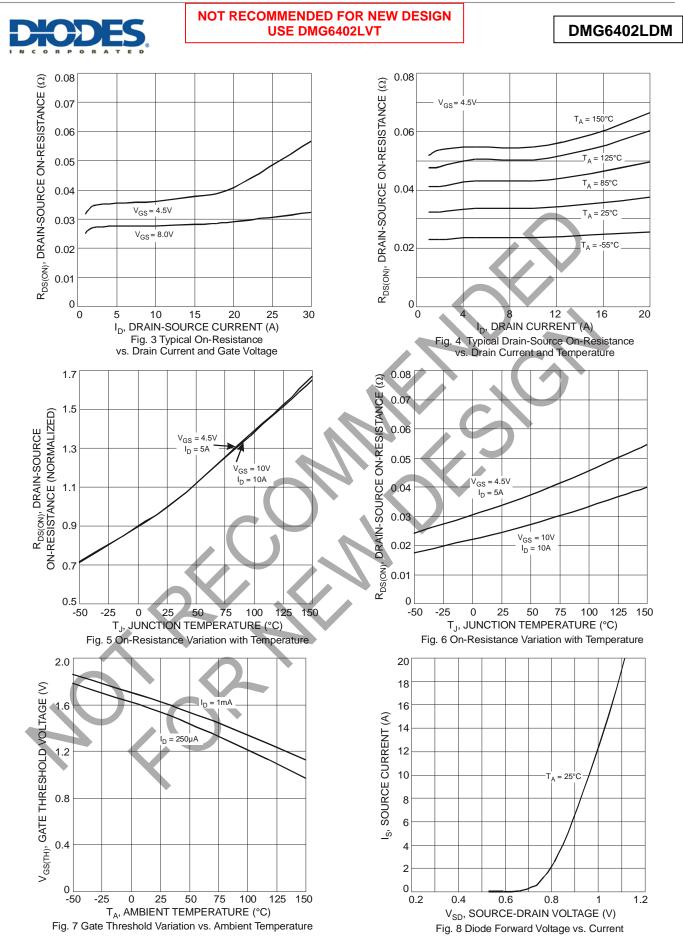
Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.



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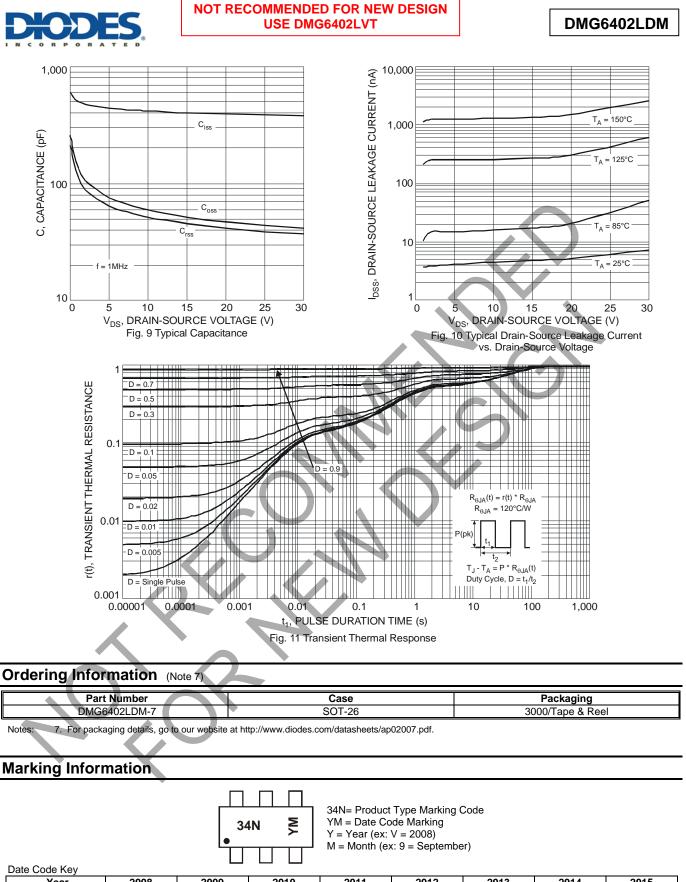


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| Year  | 2008 |     | 2009 | 2010 |     | 2011 | 2012 |     | 2013 | 2014 |     | 2015 |
|-------|------|-----|------|------|-----|------|------|-----|------|------|-----|------|
| Code  | V    |     | W    | Х    |     | Y    | Z    |     | А    | В    |     | С    |
| Month | Jan  | Feb | Mar  | Apr  | May | Jun  | Jul  | Aug | Sep  | Oct  | Nov | Dec  |
| Code  | 1    | 2   | 3    | 4    | 5   | 6    | 7    | 8   | 9    | 0    | N   | D    |

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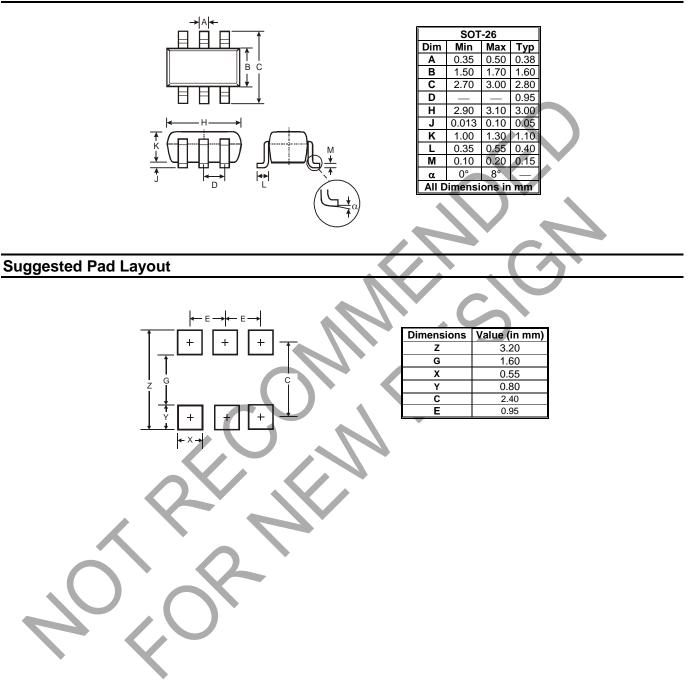
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DMG6402LDM

# Package Outline Dimensions





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